

isc Silicon PNP Power Transistor

2SA1860

DESCRIPTION

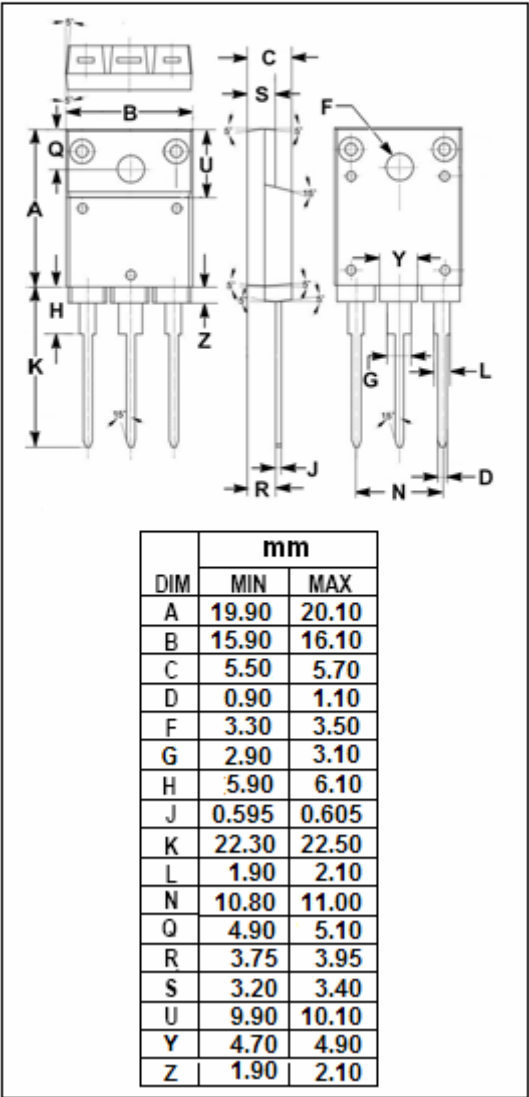
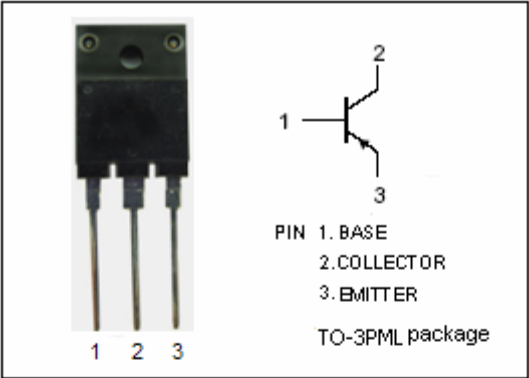
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -150V(\text{Min})$
- Good Linearity of h_{FE}
- Complement to Type 2SC4886

APPLICATIONS

- Designed for audio and general purpose applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-150	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-14	A
I_B	Base Current-Continuous	-3	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	80	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-55~150	$^{\circ}C$



isc Silicon PNP Power Transistor**2SA1860****ELECTRICAL CHARACTERISTICS****T_j=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -25mA ; I _B = 0	-150			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -5A; I _B = -0.5A			-2.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -150V ; I _E =0			-100	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V; I _C =0			-100	μ A
h _{FE}	DC Current Gain	I _C = -5A ; V _{CE} = -4V	50			
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = -10V; f= 1MHz		400		pF
f _T	Current-Gain—Bandwidth Product	I _E = 2A ; V _{CE} = -12V		50		MHz

Switching Times

t _{on}	Turn-On Time	I _C = -5A; I _{B1} = -I _{B2} = -0.5A; V _{CC} = -60V; R _L = 12 Ω		0.25		μ s
t _{stg}	Storage Time			0.85		μ s
t _f	Fall Time			0.2		μ s

◆ h_{FE} Classifications

O	P	Y
50-100	70-140	90-180